Device Modeling Report

COMPONENTS: TRANSISTOR PART NUMBER: 2SC4176-A MANUFACTURER: NEC

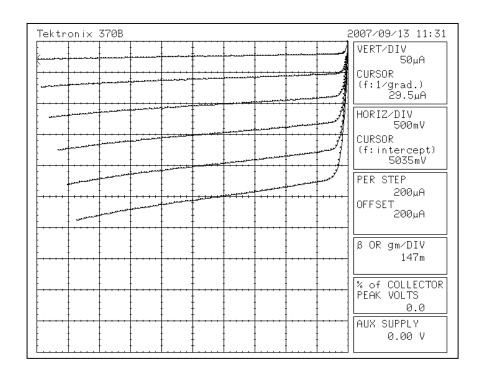


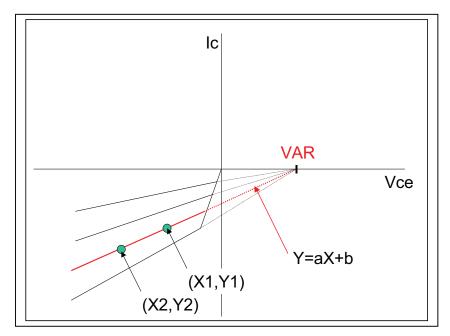
TRANSISTOR MODEL

PSpice	Model description		
model			
parameter			
IS	Saturation Current		
BF	Ideal Maximum Forward Beta		
NF	Forward Current Emission Coefficient		
VAF	Forward Early Voltage		
IKF	Forward Beta Roll-off Knee Current		
ISE	Non-ideal Base-Emitter Diode Saturation Current		
NE	Non-ideal Base-Emitter Diode Emission Coefficient		
BR	Ideal Maximum Reverse Beta		
NR	Reverse Emission Coefficient		
VAR	Reverse Early Voltage		
IKR	Reverse Beta Roll-off Knee Current		
ISC	Non-ideal Base-Collector Diode Saturation Current		
NC	Non-ideal Base-Collector Diode Emission Coefficient		
NK	Forward Beta Roll-off Slope Exponent		
RE	Emitter Resistance		
RB	Base Resistance		
RC	Series Collector Resistance		
CJE	Zero-bias Emitter-Base Junction Capacitance		
VJE	Emitter-Base Junction Potential		
MJE	Emitter-Base Junction Grading Coefficient		
CJC	Zero-bias Collector-Base Junction Capacitance		
VJC	Collector-base Junction Potential		
MJC	Collector-base Junction Grading Coefficient		
FC	Coefficient for Onset of Forward-bias Depletion		
	Capacitance		
TF	Forward Transit Time		
XTF	Coefficient for TF Dependency on Vce		
VTF	Voltage for TF Dependency on Vce		
ITF	Current for TF Dependency on Ic		
PTF	Excess Phase at f=1/2pi*TF		
TR	Reverse Transit Time		
EG	Activation Energy		
XTB	Forward Beta Temperature Coefficient		
XTI	Temperature Coefficient for IS		

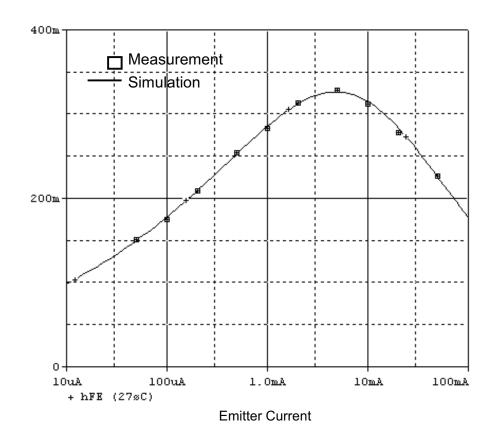
Reverse

Reverse Early Voltage Characteristic





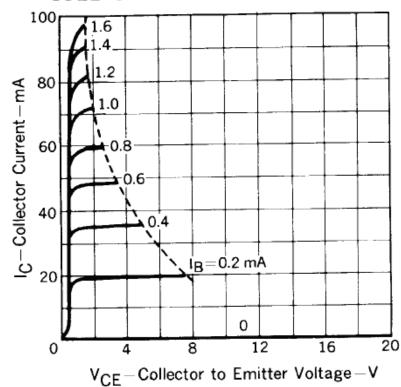
Reverse DC Beta Characteristic (le vs. hfe)

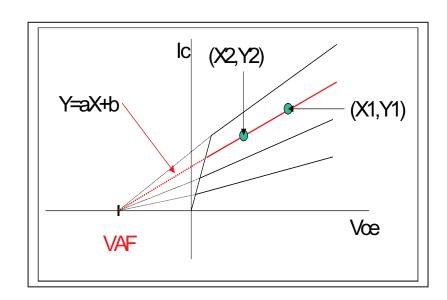


Forward

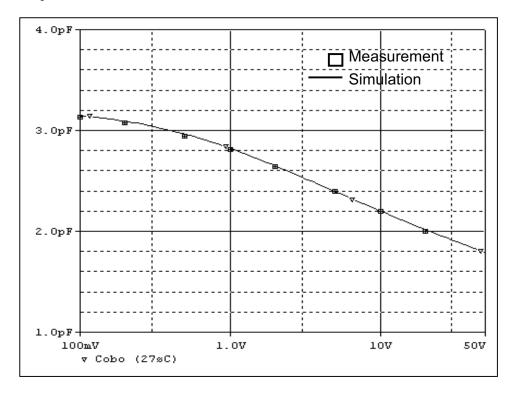
Forward Early Voltage Characteristic



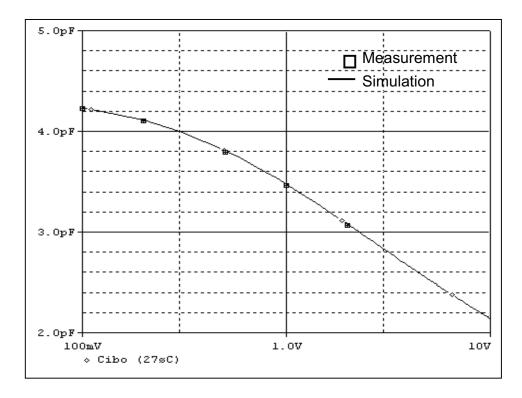




C-B Capacitance Characteristics

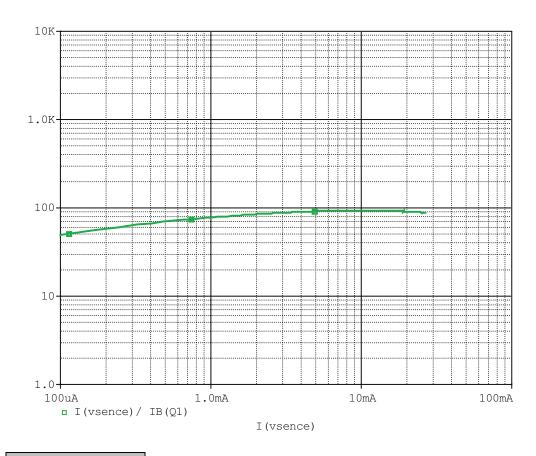


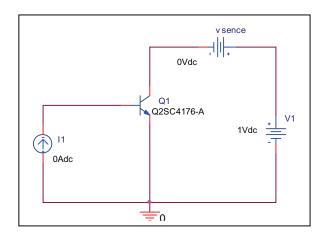
E-B Capacitance Characteristics



Transistor h_{FE}-I_C Characteristics

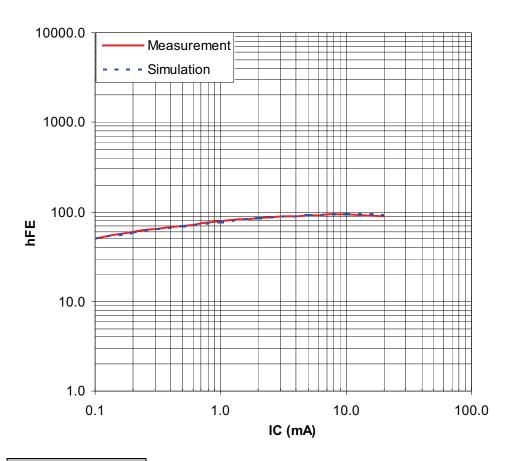
Circuit Simulation Result





Comparison Graph

Circuit Simulation Result

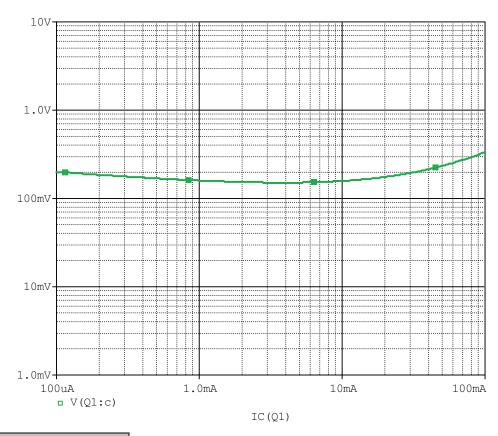


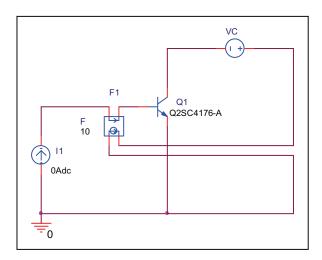
Simulation Result

Io(m A)	hFE		E====(0/)
Ic(mA)	Measurement	Simulation	Error(%)
0.100	50.000	49.881	-0.238
0.200	59.500	58.408	-1.835
0.500	70.500	69.791	-1.006
1.000	79.000	77.846	-1.461
2.000	86.000	84.872	-1.312
5.000	92.000	91.648	-0.383
10.000	93.000	93.581	0.625
20.000	90.000	91.237	1.374

V_{CE(Sat)}-I_C Characteristics

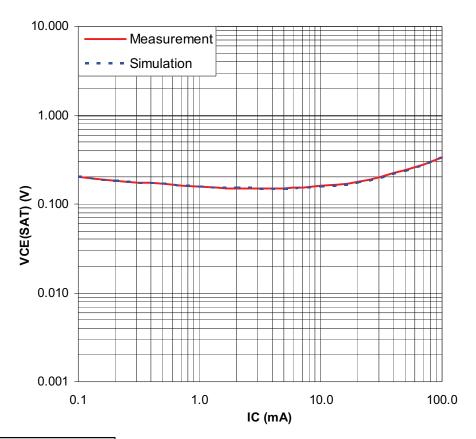
Circuit Simulation Result





Comparison Graph

Circuit Simulation Result

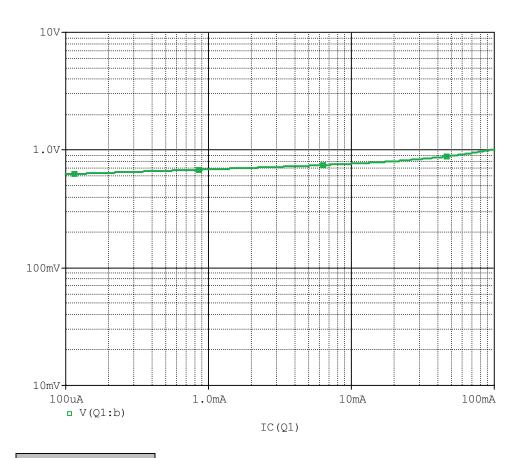


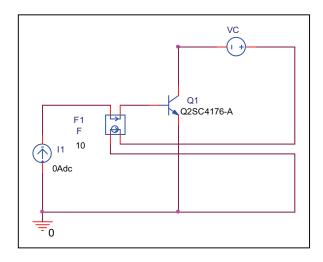
Simulation Result

IC(mA)	VCE(sat)(V)		F(0/)
	Measurement	Simulation	Error(%)
0.100	0.200	0.200	0.050
0.200	0.185	0.185	0.108
0.500	0.168	0.169	0.595
1.000	0.156	0.159	1.923
2.000	0.150	0.153	2.000
5.000	0.150	0.151	0.667
10.000	0.160	0.158	-1.438
20.000	0.180	0.175	-2.611
50.000	0.240	0.234	-2.583
100.000	0.335	0.334	-0.358

V_{BE(Sat)}-I_C Characteristics

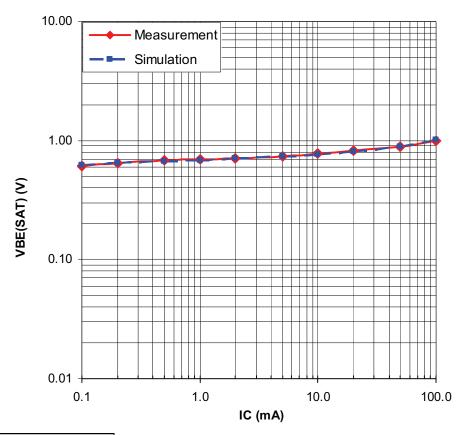
Circuit Simulation Result





Comparison Graph

Circuit Simulation Result

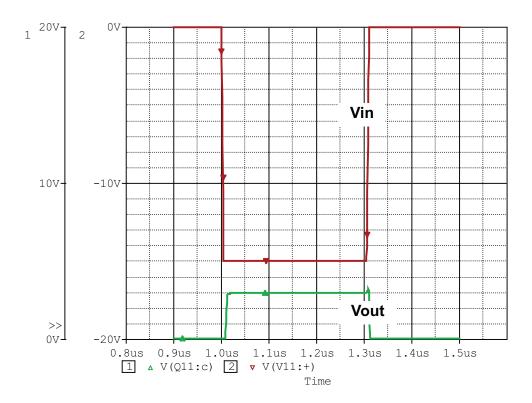


Simulation Result

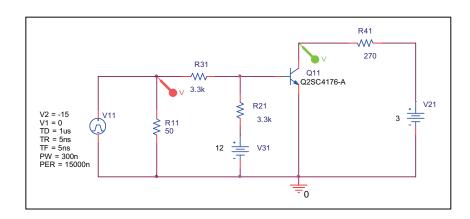
IC(mA)	VBE(sat)(V)		E === = (0/)
	Measurement	Simulation	Error(%)
0.100	0.610	0.623	2.131
0.200	0.640	0.641	0.156
0.500	0.680	0.666	-2.044
1.000	0.700	0.685	-2.114
2.000	0.710	0.705	-0.662
5.000	0.730	0.735	0.685
10.000	0.780	0.765	-1.987
20.000	0.820	0.804	-1.951
50.000	0.880	0.891	1.250
100.000	1.000	1.015	1.500

Switching Characteristics (toff)

Circuit simulation result



Evaluation circuit

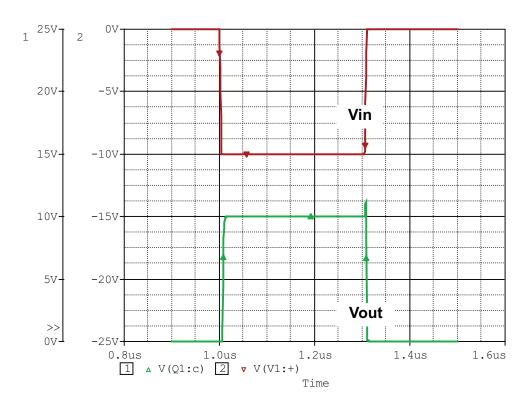


Simulation result

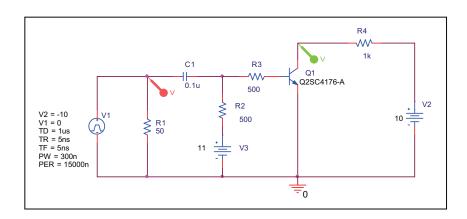
	Measurement	Simulation	%Error
t _{off} (ns)	12.000	12.149	1.242

Switching Characteristics (tstg)

Circuit simulation result



Evaluation circuit



Simulation result

	Measurement	Simulation	%Error
t _{stg} (ns)	6.000	6.015	0.253

Output Characteristics

Circuit Simulation Result

